

Silicon NPN Power Transistors

2SD1276 2SD1276A

DESCRIPTION

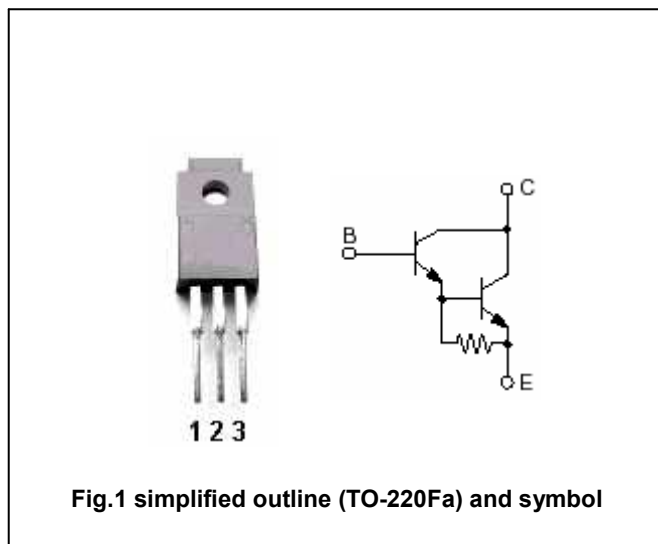
- With TO-220Fa package
- Complement to type 2SB950/950A
- High DC current gain
- High-speed switching

APPLICATIONS

- For power amplification

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SD1276	Open emitter	60	V
		2SD1276A		80	
V_{CEO}	Collector-emitter voltage	2SD1276	Open base	60	V
		2SD1276A		80	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current (DC)			4	A
I_{CM}	Collector current-Peak			8	A
P_C	Collector power dissipation		$T_C=25$	40	W
			$T_a=25$	2	
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SD1276	$I_C=30mA, I_B=0$	60			V
		2SD1276A		80			
$V_{CEsat-1}$	Collector-emitter saturation voltage		$I_C=3A; I_B=12mA$			2	V
V_{CEsat-}	Collector-emitter saturation voltage		$I_C=5A; I_B=20mA$			4	V
V_{BE}	Base-emitter voltage		$V_{CE}=3V; I_C=3A$			2.5	V
I_{CBO}	Collector cut-off current	2SD1276	$V_{CB}=60V; I_E=0$			0.2	mA
		2SD1276A	$V_{CB}=80V; I_E=0$				
I_{CEO}	Collector cut-off current	2SD1276	$V_{CE}=30V; I_B=0$			0.5	mA
		2SD1276A	$V_{CE}=40V; I_B=0$				
I_{EBO}	Emitter cut-off current		$V_{EB}=5V; I_C=0$			2	mA
h_{FE-1}	DC current gain		$I_C=3A; V_{CE}=0.5V$	1000			
h_{FE-2}	DC current gain		$I_C=3A; V_{CE}=3V$	2000		10000	
f_T	Transition frequency		$I_C=0.5A; V_{CE}=10V; f=1MHz$		20		MHz

Switching times

t_{on}	Turn-on time	$I_C=2A; I_{B1}=8mA$ $I_{B2}=-8mA; V_{CC}=50V$		0.5		μs
t_s	Storage time			4		μs
t_f	Fall time			1		μs

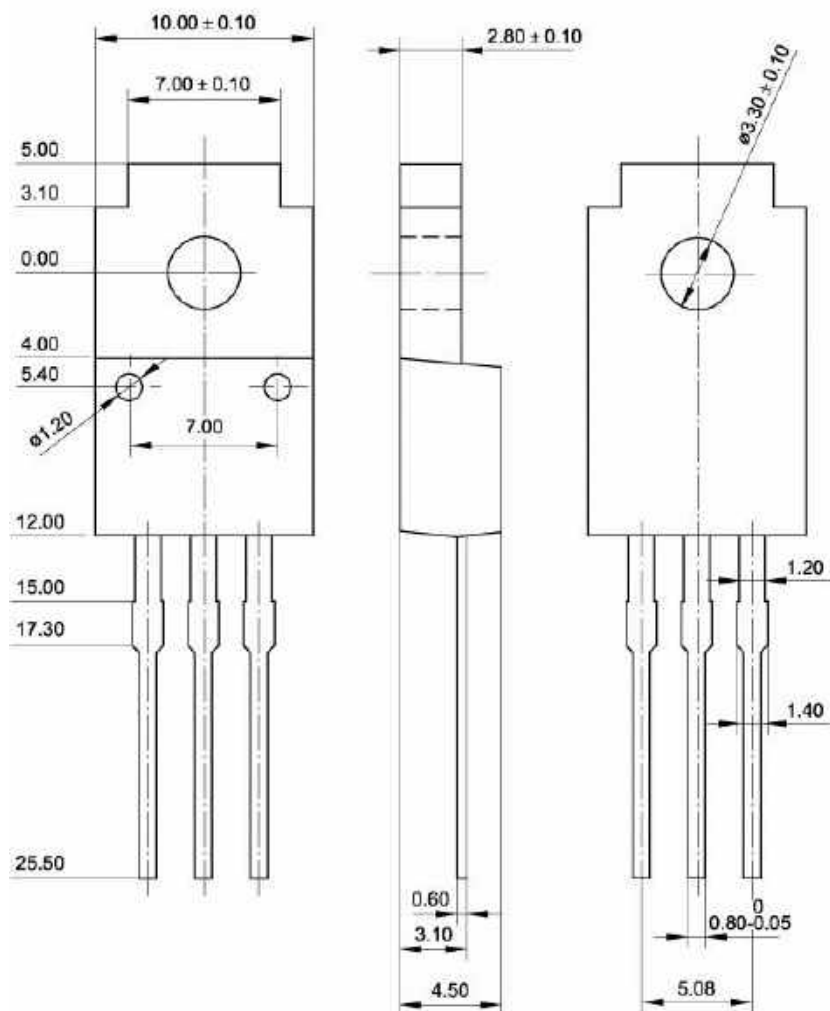
◆ h_{FE-2} Classifications

Q	R
2000-5000	4000-10000

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)